

GM1300

PNP SILICON EPITAXIAL TRANSISTOR

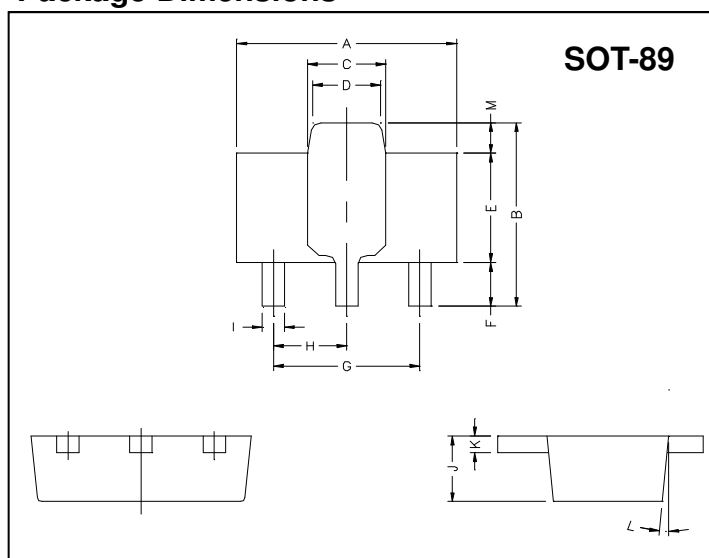
Description

The GM1300 is designed for medium power amplifier applications.

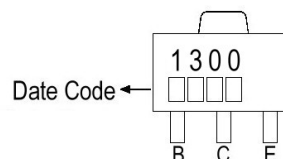
Features

- $h_{FE(1)}=140\sim1000$ ($@V_{CE}=-1V, I_C=-0.5A$)
- $h_{FE(2)}=60$ (Min.) ($@V_{CE}=-1V, I_C=-2A$)
- Low Saturation Voltage $V_{CE(sat)}=-0.5$ (Max.) ($@I_C=-2A, I_B=-50mA$)

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55~+150	$^\circ C$
Collector to Base Voltage	V_{CBO}	-20	V
Collector to Emitter Voltage	V_{CEO}	-10	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current (DC)	I_C	-2	A
Collector Current (Pulse)	I_C	-5	A
Base Current	I_B	-200	mA
Total Power Dissipation	P_D	1	W

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise stated)

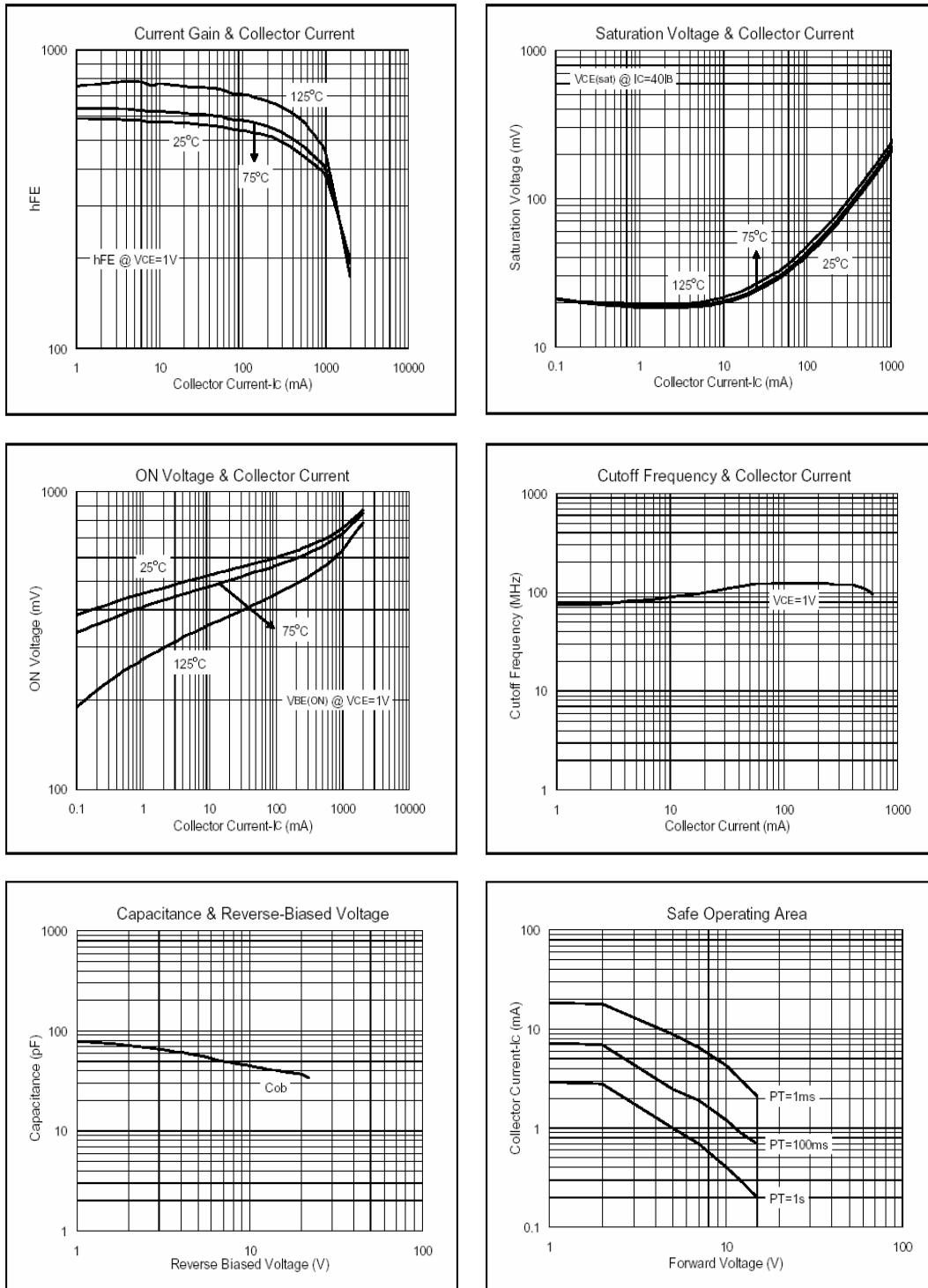
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	-20	-	-	V	$I_C=-100\mu A, I_E=0$
V_{CEO}	-10	-	-	V	$I_C=-10mA, I_B=0$
V_{EBO}	-6	-	-	V	$I_E=-1mA, I_C=0$
I_{CBO}	-	-	-100	nA	$V_{CB}=-20V, I_E=0$
I_{CES}	-	-	-100	nA	$V_{CES}=-20V$
I_{EBO}	-	-	-100	nA	$V_{EB}=-6V, I_C=0$
$*V_{CE(sat)}$	-	-0.3	-0.5	V	$I_C=-2A, I_B=-50mA$
$*V_{BE(on)}$	-	-0.83	-1.5	V	$V_{CE}=-1V, I_C=-2A$
$*h_{FE1}$	140	-	1000		$V_{CE}=-1V, I_C=-0.5A$
$*h_{FE2}$	60	-	-		$V_{CE}=-1V, I_C=-2A$
fT	-	140	-	MHz	$V_{CE}=-1V, I_C=-0.5A, f=100MHz$
Cob	-	50	-	pF	$V_{CB}=-10V, I_E=0, f=1MHz$

* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE1}

Rank	Y	GR	BL	PE
Range	140 ~ 280	200 ~ 400	300 ~ 600	500 ~ 1000

Characteristics Curve



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